TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

T C 7 M A 2 4 5 F K

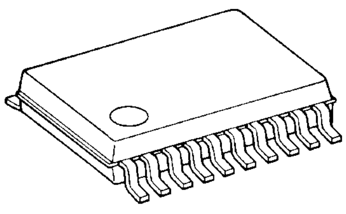
Low-Voltage Octal Bus Transceiver with 3.6 V Tolerant Inputs and Outputs

The TC7MA245FK is a high performance CMOS octal bus transceiver. Designed for use in 1.8 , 2.5 or 3.3 V systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to 3.6 V.

The direction of data transmission is determined by the level of the DIR inputs. The $\overline{OE}$ inputs can be used to disable the device so that the busses are effectively isolated.

All inputs are equipped with protection circuits against static discharge.



VSSOP20-P-0030-0.50

Weight: 0.03 g (typ.)

Features

- Low voltage operation: V_{CC} = 1.8~3.6 V
- High speed operation:
  - t_{pd} = 3.5 ns (max) (V_{CC} = 3.0~3.6 V)
  - t_{pd} = 4.2 ns (max) (V_{CC} = 2.3~2.7 V)
  - t_{pd} = 8.4 ns (max) (V_{CC} = 1.8 V)
- 3.6 V tolerant inputs and outputs.
- Package: VSSOP (US20)
- Output current:
  - I_{OH}/I_{OL} = ±24 mA (min) (V_{CC} = 3.0 V)
  - I_{OH}/I_{OL} = ±18 mA (min) (V_{CC} = 2.3 V)
  - I_{OH}/I_{OL} = ±6 mA (min) (V_{CC} = 1.8 V)
- Latch-up performance: ±300 mA
- ESD performance:
  - Machine model > ±200 V
  - Human body model > ±2000 V
- Bidirectional interface between 2.5 V and 3.3 V signals. (*1)
- Power down protection is provided on all inputs and outputs. (*2)
- Supports live insertion/withdrawal (*3)

*1: Do not apply a signal to any bus terminal when it is in the output mode. Damage may result.

*2: All floating (high impedance) bus terminal must have their input level fixed by means of pull up or pull down resistors.

*3: To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

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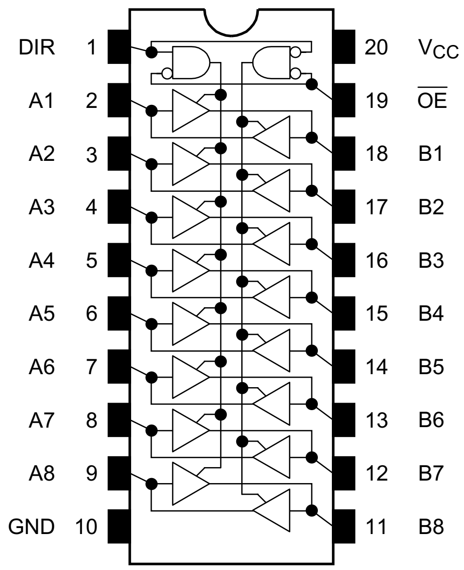
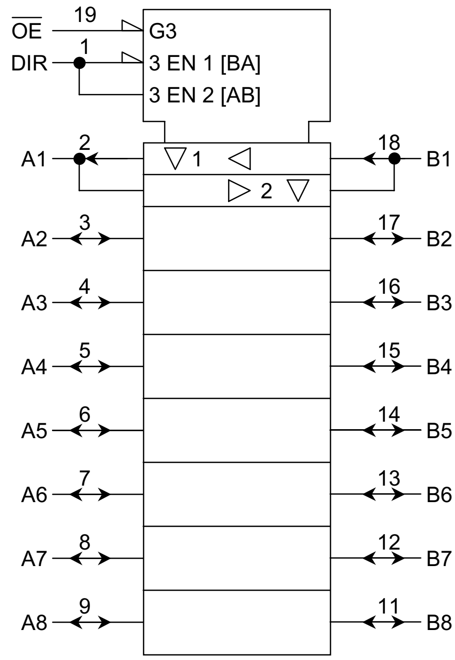
Pin Assignment (top view)



IEC Logic Symbol



Truth Table

Inputs		Outputs	Function	
$\overline{OE}$	DIR		A-Bus	B-Bus
L	L	A = B	Output	Input
L	H	B = A	Input	Output
H	X	Z	Z	

X: Don't care

Z: High impedance

Maximum Ratings

Characteristics	Symbol	Rating	Unit
Power supply voltage	V_{CC}	−0.5~4.6	V
DC input voltage (DIR, $\overline{OE}$)	V_{IN}	−0.5~4.6	V
DC bus I/O voltage	$V_{I/O}$	−0.5~4.6 (Note1)	V
		−0.5~V_{CC} + 0.5 (Note2)	
Input diode current	I_{IK}	−50	mA
Output diode current	I_{OK}	±50 (Note3)	mA
DC output current	I_{OUT}	±50	mA
Power dissipation	P_D	180	mW
DC V_{CC}/ground current	I_{CC}/I_{GND}	±100	mA
Storage temperature	T_{stg}	−65~150	°C

Note1: Off-state

Note2: High or low state. I_{OUT} absolute maximum rating must be observed.

Note3: $V_{OUT} < GND$, $V_{OUT} > V_{CC}$

Recommended Operating Range

Characteristics	Symbol	Rating	Unit
Supply voltage	V_{CC}	1.8~3.6	V
		1.2~3.6 (Note4)	
Input voltage (DIR, $\overline{OE}$)	V_{IN}	−0.3~3.6	V
Bus I/O voltage	$V_{I/O}$	0~3.6 (Note5)	V
		0~V_{CC} (Note6)	
Output current	I_{OH}/I_{OL}	±24 (Note7)	mA
		±18 (Note8)	
		±6 (Note9)	
Operating temperature	T_{opr}	−40~85	°C
Input rise and fall time	dt/dv	0~10 (Note10)	ns/V

Note4: Data retention only

Note5: Off-state

Note6: High or low state

Note7: V_{CC} = 3.0~3.6 V

Note8: V_{CC} = 2.3~2.7 V

Note9: V_{CC} = 1.8 V

Note10: V_{IN} = 0.8~2.0 V, V_{CC} = 3.0 V

Electrical Characteristics

DC Characteristics (Ta = –40~85°C, 2.7 V < V_{CC} ≦ 3.6 V)

Characteristics		Symbol	Test Condition		V_{CC} (V)	Min	Max	Unit
Input voltage	High level	V_{IH}	—		2.7~3.6	2.0	—	V
	Low level	V_{IL}	—		2.7~3.6	—	0.8	
Output voltage	High level	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	I_{OH} = –100 μA	2.7~3.6	V_{CC} – 0.2	—	V
				I_{OH} = –12 mA	2.7	2.2	—	
				I_{OH} = –18 mA	3.0	2.4	—	
				I_{OH} = –24 mA	3.0	2.2	—	
	Low level	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	I_{OL} = 100 μA	2.7~3.6	—	0.2	
				I_{OL} = 12 mA	2.7	—	0.4	
				I_{OL} = 18 mA	3.0	—	0.4	
				I_{OL} = 24 mA	3.0	—	0.55	
Input leakage current		I_{IN}	V_{IN} = 0~3.6 V		2.7~3.6	—	±5.0	μA
3-state output off-state current		I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} V_{OUT} = 0~3.6 V		2.7~3.6	—	±10.0	μA
Power off leakage current		I_{OFF}	V_{IN}, V_{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent supply current		I_{CC}	$V_{IN} = V_{CC}$ or GND		2.7~3.6	—	20.0	μA
			V_{CC} ≦ (V_{IN}, V_{OUT}) ≦ 3.6 V		2.7~3.6	—	±20.0	
Increase in I_{CC} per input		ΔI_{CC}	$V_{IH} = V_{CC}$ – 0.6 V		2.7~3.6	—	750	

DC Characteristics (Ta = –40~85°C, 2.3 V ≦ V_{CC} ≦ 2.7 V)

Characteristics		Symbol	Test Condition		V_{CC} (V)	Min	Max	Unit
Input voltage	High level	V_{IH}	—		2.3~2.7	1.6	—	V
	Low level	V_{IL}	—		2.3~2.7	—	0.7	
Output voltage	High level	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	I_{OH} = –100 μA	2.3~2.7	V_{CC} – 0.2	—	V
				I_{OH} = –6 mA	2.3	2.0	—	
				I_{OH} = –12 mA	2.3	1.8	—	
				I_{OH} = –18 mA	2.3	1.7	—	
	Low level	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	I_{OL} = 100 μA	2.3~2.7	—	0.2	
				I_{OL} = 12 mA	2.3	—	0.4	
				I_{OL} = 18 mA	2.3	—	0.6	
Input leakage current		I_{IN}	V_{IN} = 0~3.6 V		2.3~2.7	—	±5.0	μA
3-state output off-state current		I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} V_{OUT} = 0~3.6 V		2.3~2.7	—	±10.0	μA
Power off leakage current		I_{OFF}	V_{IN}, V_{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent supply current		I_{CC}	$V_{IN} = V_{CC}$ or GND		2.3~2.7	—	20.0	μA
			V_{CC} ≦ (V_{IN}, V_{OUT}) ≦ 3.6 V		2.3~2.7	—	±20.0	

DC Characteristics (Ta = –40~85°C, 1.8 V ≦ V_{CC} < 2.3 V)

Characteristics		Symbol	Test Condition		V_{CC} (V)	Min	Max	Unit
Input voltage	High level	V_{IH}	—		1.8~2.3	0.7 × V_{CC}	—	V
	Low level	V_{IL}	—		1.8~2.3	—	0.2 × V_{CC}	
Output voltage	High level	V_{OH}	V_{IN} = V_{IH} or V_{IL}	I_{OH} = –100 μA	1.8	V_{CC} – 0.2	—	V
				I_{OH} = –6 mA	1.8	1.4	—	
	Low level	V_{OL}	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 100 μA	1.8	—	0.2	
				I_{OL} = 6 mA	1.8	—	0.3	
Input leakage current		I_{IN}	V_{IN} = 0~3.6 V		1.8	—	±5.0	μA
3-state output off-state current		I_{OZ}	V_{IN} = V_{IH} or V_{IL} V_{OUT} = 0~3.6 V		1.8	—	±10.0	μA
Power off leakage current		I_{OFF}	V_{IN}, V_{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent supply current		I_{CC}	V_{IN} = V_{CC} or GND		1.8	—	20.0	μA
			V_{CC} ≦ (V_{IN}, V_{OUT}) ≦ 3.6 V		1.8	—	±20.0	

AC Characteristics (Ta = –40~85°C, Input: $t_r = t_f$ = 2.0 ns, C_L = 30 pF, R_L = 500 Ω)

Characteristics	Symbol	Test Condition	V_{CC} (V)	Min	Max	Unit
Propagation delay time	t_{pLH} t_{pHL}	Figure 1, Figure 2	1.8	1.5	8.4	ns
			2.5 ± 0.2	0.8	4.2	
			3.3 ± 0.3	0.6	3.5	
3-state output enable time	t_{pZL} t_{pZH}	Figure 1, Figure 3	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	5.6	
			3.3 ± 0.3	0.6	4.5	
3-state output disable time	t_{pLZ} t_{pHZ}	Figure 1, Figure 3	1.8	1.5	7.2	ns
			2.5 ± 0.2	0.8	4.0	
			3.3 ± 0.3	0.6	3.6	
Output to output skew	t_{osLH} t_{osHL}	(Note11)	1.8	—	0.5	ns
			2.5 ± 0.2	—	0.5	
			3.3 ± 0.3	—	0.5	

For C_L = 50 pF, add approximately 300 ps to the AC maximum specification.

Note11: This parameter is guaranteed by design.
($t_{osLH} = |t_{pLHm} - t_{pLHn}|$, $t_{osHL} = |t_{pHLm} - t_{pHLn}|$)

Dynamic Switching Characteristics (Ta = 25°C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF)

Characteristics	Symbol	Test Condition		V_{CC} (V)	Typ.	Unit
Quiet output maximum dynamic V_{OL}	V_{OLP}	$V_{IH} = 1.8$ V, $V_{IL} = 0$ V	(Note12)	1.8	0.25	V
		$V_{IH} = 2.5$ V, $V_{IL} = 0$ V	(Note12)	2.5	0.6	
		$V_{IH} = 3.3$ V, $V_{IL} = 0$ V	(Note12)	3.3	0.8	
Quiet output minimum dynamic V_{OL}	V_{OLV}	$V_{IH} = 1.8$ V, $V_{IL} = 0$ V	(Note12)	1.8	–0.25	V
		$V_{IH} = 2.5$ V, $V_{IL} = 0$ V	(Note12)	2.5	–0.6	
		$V_{IH} = 3.3$ V, $V_{IL} = 0$ V	(Note12)	3.3	–0.8	
Quiet output minimum dynamic V_{OH}	V_{OHV}	$V_{IH} = 1.8$ V, $V_{IL} = 0$ V	(Note12)	1.8	1.5	V
		$V_{IH} = 2.5$ V, $V_{IL} = 0$ V	(Note12)	2.5	1.9	
		$V_{IH} = 3.3$ V, $V_{IL} = 0$ V	(Note12)	3.3	2.2	

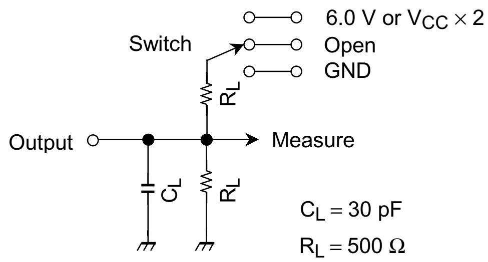
Note12: This parameter is guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition		V_{CC} (V)	Typ.	Unit
Input capacitance	C_{IN}	—		1.8, 2.5, 3.3	6	pF
Bus I/O capacitance	$C_{I/O}$	—		1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C_{PD}	$f_{IN} = 10$ MHz	(Note13)	1.8, 2.5, 3.3	20	pF

Note13: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.
Average operating current can be obtained by the equation:
$I_{CC\ (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8$ (per bit)

AC Test Circuit



Parameter	Switch
t_{pLH}, t_{pHL}	Open
t_{pLZ}, t_{pZL}	6.0 V @V_{CC} = 3.3 ± 0.3 V V_{CC} × 2 @V_{CC} = 2.5 ± 0.2 V @V_{CC} = 1.8 V
t_{pHZ}, t_{pZH}	GND

Figure 1

AC Waveform

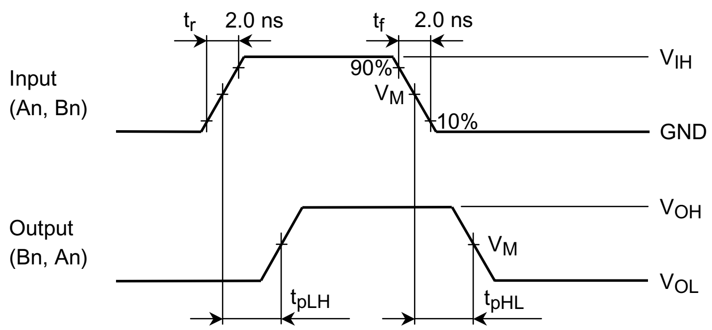
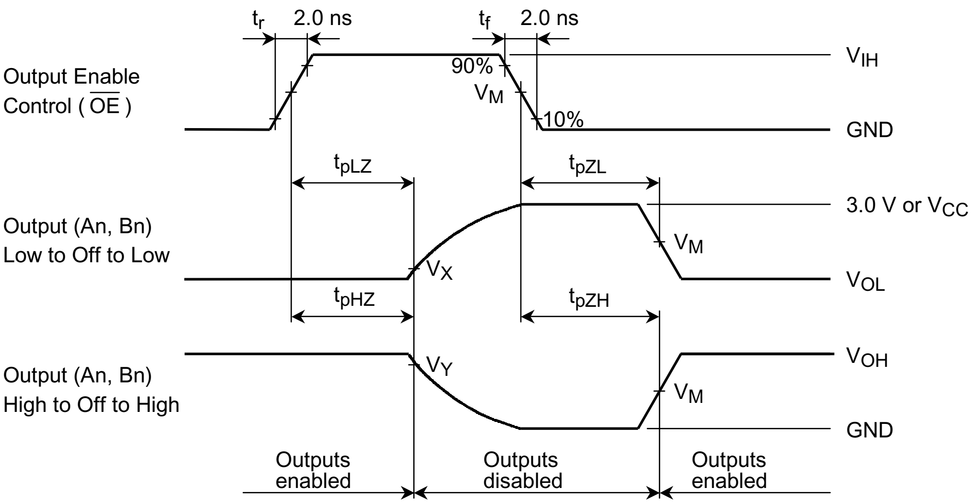


Figure 2 t_{pLH}, t_{pHL}

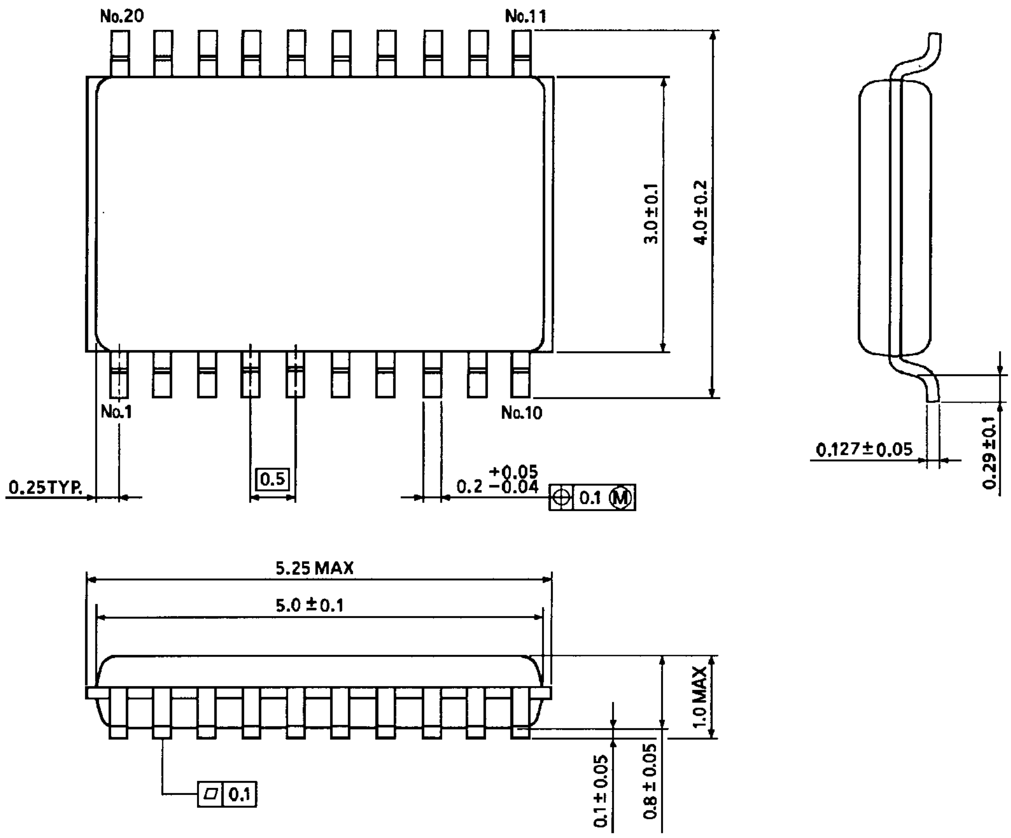


Symbol	V_{CC}		
	3.3 ± 0.3 V	2.5 ± 0.2 V	1.8 V
V_{IH}	2.7 V	V_{CC}	V_{CC}
V_M	1.5 V	$V_{CC}/2$	$V_{CC}/2$
V_X	V_{OL} + 0.3 V	V_{OL} + 0.15 V	V_{OL} + 0.15 V
V_Y	V_{OH} − 0.3 V	V_{OH} − 0.15 V	V_{OH} − 0.15 V

Figure 3 t_{pLZ}, t_{pHZ}, t_{pZL}, t_{pZH}

Package Dimensions

VSSOP20-P-0030-0.50 Unit : mm



Weight: 0.03 g (typ.)